

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

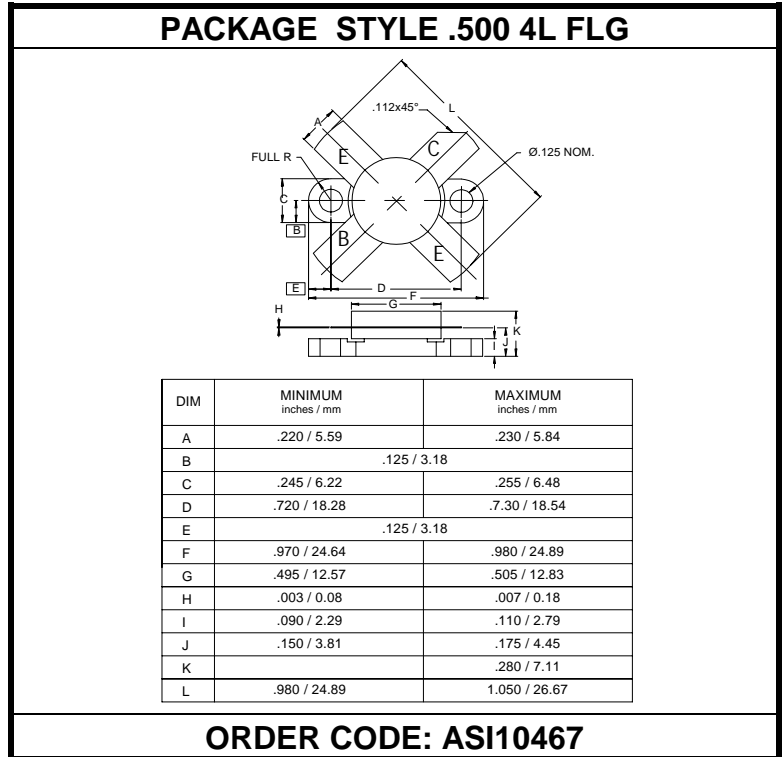
The **ASI MRF427** is Designed for high voltage applications up to 30 MHz

FEATURES:

- $P_G = 18$ dB min. at 25 W/30 MHz
- $IMD_3 = -34$ dBc max. at 25 W_(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.0 A
V_{CBO}	110 V
V_{CEO}	65 V
V_{EBO}	4.0 V
P_{DISS}	80 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	2.19 $^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 100$ mA	110			V
BV_{CES}	$I_C = 100$ mA	110			V
BV_{CEO}	$I_C = 200$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		90	---
C_{ob}	$V_{CB} = 50$ V $f = 1.0$ MHz			60	pF
G_P IMD_3	$V_{CE} = 50$ V $P_{OUT} = 25$ W (PEP) $f = 30$ MHz	18	20 - 37	-34	dB dBc